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Effect of the Si excess on the structure and the optical properties of Nd-doped Si-rich silicon oxide

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ABSTRACT

Nd-doped Si-rich silicon oxide thin films were produced by radio frequency magnetron co-sputtering of three confocal cathodes: Si, SiO₂, and Nd₂O₃, in pure argon plasma at 500 °C. The microstructure and optical properties of the films were investigated versus silicon excess and post-deposition annealing treatment by means of ellipsometry and Fourier transform infrared spectrometry as well as by the photoluminescence method. A notable emission from Nd³⁺ ions was obtained for the as-deposited sample, while the films annealed at 900 °C showed the highest peak intensity. The maximum emission was observed for the films with 4.7 at% of Si excess.

Keywords:

Si-rich-silicon oxide
Neodymium
Magnetron sputtering
Refractive index
Infrared absorption
Photoluminescence

1. Introduction

During last decade a great research effort has been focused on the development of the Si-based nanostructured materials for photonic application [1–5]. Among them, Si nanoclusters (Si-ncs) embedded in SiO₂ host are widely studied due to an achievement of room-temperature light emission from the blue to the infrared depending on the Si-ncs size [6,7].

Rare-earth (RE) ions possess narrow emission lines and receive more and more interest from the scientists in the world [8]. RE doped silica is a well-known medium for laser application, but its use requires high-power sources to achieve an efficient emission. Considerable attention was paid to silica co-doped with RE ions and Si-ncs since (i) such nanocomposite materials can be pumped using broadband sources due to the spectrally wide absorption of Si-ncs and (ii) Si-ncs are found to be efficient sensitizers of RE ions.

In this regard, the most studied materials are Er-doped Si-rich silicon oxide (SRSO) due to promising application as a source for optical communication. In previous works [9–15] a significant enhancement of photoluminescence (PL) intensity of the intra-4f shell transition of Er³⁺ due to the energy transfer from Si-ncs to RE ions has been demonstrated. The detailed study of the excitation mechanism of Er³⁺ ions showed that the excitation rate depends on the Si-ncs size and becomes higher for the smaller Si-ncs [16].

In the contrast of well-studied Er-SRSO system, other RE ions are not well-addressed. On the contrary to Er³⁺ ions, the doping

of SRSO with Nd³⁺ ions is most promising due to overlapping of 4f-shell absorption transitions with the range of intrinsic Si-ncs PL. Moreover, Nd³⁺ ions offer very important light emission in the infrared spectral range at 1.06 and 1.32 μm in a four-level system configuration which avoid re-absorption of the emitted radiation. The benefits of Si-nc sensitizers towards Nd³⁺ ions was already demonstrated [17,18]. However, its improvement requires a special attention to some critical parameters as the coupling rate between Nd³⁺ ions and Si-ncs as well as the quality of the surrounded host medium aiming significant decrease of the non-radiative channels contribution. In the former case, the coupling rate can be monitored via the Nd³⁺ ions content and the Si excess (Si_{ex}) concentration. The latter has a direct influence on the number of Si-ncs embedded in SiO₂ as well as on the host quality.

In this study, both the structure and the optical properties of Nd-doped SRSO thin films were investigated versus Si_{ex} and the annealing treatment in order to obtain high efficient of Nd³⁺ light emission via energy transfer from Si-ncs toward Nd³⁺ ions.

2. Experimental techniques

The samples were deposited onto p-type silicon wafers by radio frequency magnetron co-sputtering of three confocal cathodes: Si, SiO₂, and Nd₂O₃, in a pure argon plasma. The substrate was rotated during the deposition to ensure a high homogeneity of the film. The deposition temperature and the total plasma pressure were kept at 500 °C and 3 mTorr, respectively. The power density applied on the SiO₂ and the Nd₂O₃ cathodes were fixed at 8.88 and 0.30 W/cm², respectively, whereas the power density applied on the Si cathode, P_{Si}, was varied from 0.74 to

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2.37 W/cm². The deposition time was tuned to achieve the film thickness in the 250–300 nm range for avoiding the effect of the film stresses on the optical parameters [19]. An annealing treatment was performed in a conventional furnace at 900 and 1100 °C during 1 h in a nitrogen flow. Spectroscopic ellipsometry was used to determine the optical constants: thickness and refractive index n of the films. The data were collected by means of a Jobin–Yvon ellipsometer (UVISSEL) where the incident light was scanned in the 1.5–4.5 eV range under an incident angle of 66.3°. The fitting of the experimental data was performed using DeltaPsi2 software [20].

The sample's infrared absorption properties were investigated by means of a Nicolet Nexus Fourier transform infrared (FTIR) spectrometer. The spectra were acquired under normal and Brewster angle incidence (65°). The PL spectra were recorded with a photomultiplier tube Hamamatsu (R5108) after dispersion of the PL signal with a Jobin–Yvon TRIAX 180 monochromator using an Ar⁺ laser operated at 488 nm which is a non-resonant wavelength for Nd³⁺ excitation. For this study, we focused our PL experiment in the visible-near infrared range (600–1000 nm) to analyze the unique contribution of the RE ions in the de-excitation process [17].

3. Results and discussion

3.1. The Si_{ex} estimation

Fig. 1 displays the evolutions of the refractive index n and the TO₃ peak position of Si–O vibration bond as a function of P_{Si} for as-deposited samples. The n value increases from 1.48 to 1.70 with P_{Si} . According to the effective medium approximation (EMA) and using the Bruggeman model theory [21–23], the O/Si ratio (x) can be determined from the following equation:

$$x = \frac{-36n^4 + 691n^2 + 773}{22n^4 + 665n^2 - 472} \quad (1)$$

To note that the n value is given at 1.95 eV, and during the deducing of Eq. (1), $n_{a-si} = 4.498$ and $n_{SiO_2} = 1.457$ are used.

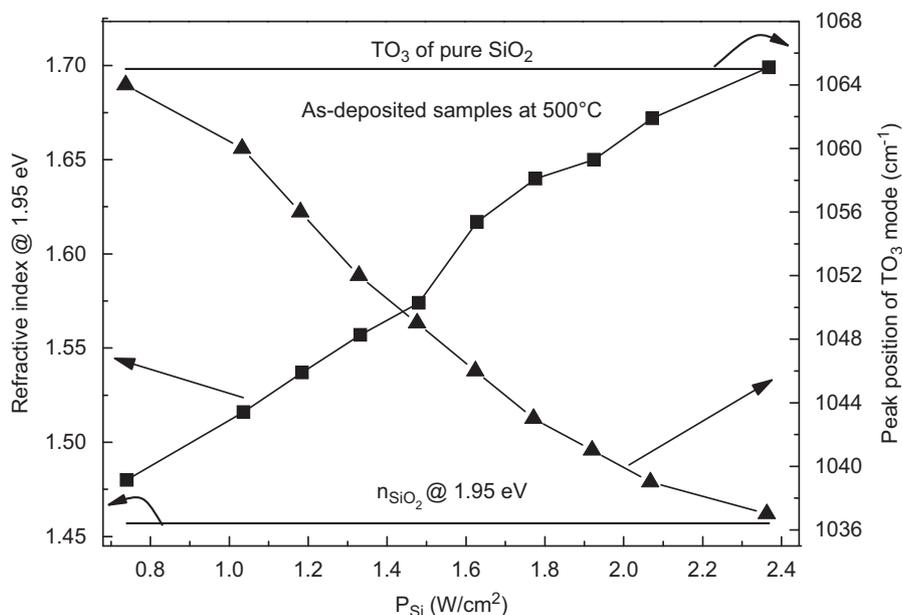


Fig. 1. Evolution of the refractive index n taken at 1.95 eV energy (left axis) and of the TO₃ Si–O peak position (right axis) versus P_{Si} for as-deposited samples. The lines on top and bottom are the TO₃ position (1065 cm⁻¹) and the refractive index n (1.457) for pure SiO₂ grown at the same conditions with the same thickness as SRSO–Nd layers, respectively.

Furthermore, the peak position of the TO₃ mode in Fig. 1 decreases almost linearly with the increased P_{Si} . On the basis of the following equation [24]:

$$x = 0.02v - 19.3 \quad (2)$$

v is the TO₃ peak position of sample SiO _{x} , one can obtain the x value. For this pure SiO₂ layer was grown at the same conditions as SRSO–Nd layers and had the same thickness. This approach gives more accurate estimation than the comparison with the TO₃ peak position of SiO₂ (~1080 cm⁻¹) published elsewhere [25].

Thereafter, Si_{ex} (at%) was calculated from x using the following equation:

$$Si_{ex}(\text{at}\%) = \frac{2-x}{2+2x} 100 \quad (3)$$

And the results of Si_{ex} estimated from both FTIR and EMA are shown in Fig. 2. It is worth to note that the Si_{ex} values obtained by the two methods are in good agreement within uncertainty.

3.2. Effect of annealing treatment on the microstructure

Fig. 3 shows a typical evolution of the FTIR spectra recorded at the Brewster incidence for films ($P_{Si} = 1.33$ W/cm²) as-deposited and annealed at 900 and 1100 °C. This film was chosen as a typical one to study for its highest emission from Nd³⁺ ions discussed later. The spectra are normalized with respect to the TO₃ phonon mode intensity. It is found that the TO₃ peak position shifts from 1050 to 1080 cm⁻¹ with the increasing annealing temperature (T_A). This great shift is explained by the condensation and agglomeration of the Si_{ex} resulting in the formation of Si–ncs [26] at the expense of volumic silica. The evolution of FTIR spectra is a confirmation of the formation of SiO₂ and Si phases via phase separation in the SiO _{x} host [25]. Moreover, the intensity of the LO₃ peak increases and the intensity of the LO₄–TO₄ pair mode attenuates with the increase of T_A . The former is a signature of the improvement of the Si/SiO _{x} interface [27], whereas the latter indicates a reduction in disorder of the host.

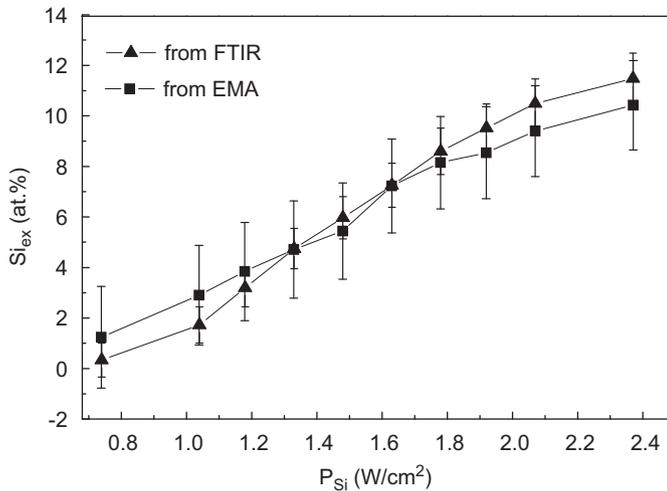


Fig. 2. Evolution of Si_{ex} (at.%) as a function of P_{Si} for as-deposited samples.

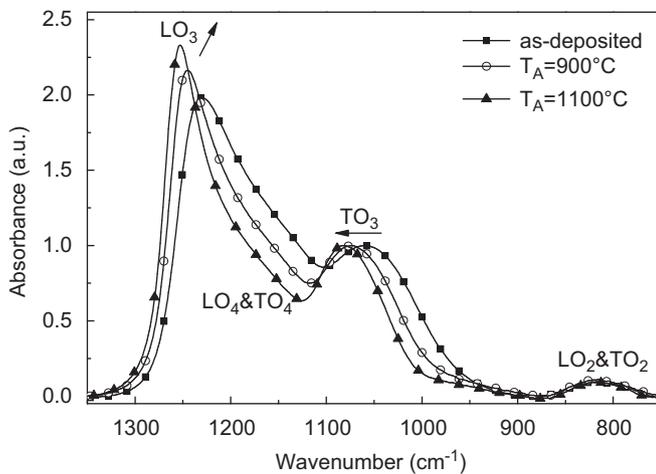


Fig. 3. Typical evolution of the FTIR spectra measured in Brewster incidence for as-deposited and annealed films.

3.3. Photoluminescence properties

The film with $P_{\text{Si}}=1.33 \text{ W/cm}^2$ was once more chosen to demonstrate the evolution of light emission properties versus an annealing treatment. The room temperature PL spectra of sample as-deposited and annealed at 900 and 1100 °C are shown in Fig. 4. It is seen that the sample annealed at 1100 °C emits a broad PL band in the visible domain that can be ascribed to radiative carrier recombination in Si-ncs.

As one can also see from Fig. 4, no emission was detected in this range for both as-deposited and 900 °C-annealed sample. However, this latter FTIR spectrum (Fig. 3) shows a phase separation process and thus the presence of Si-ncs. We conclude that the visible emission is quenched either due to energy transfer or to defect in the host [28]. This assumption is confirmed by the analysis of the Nd^{3+} PL bands (Fig. 4).

In the infrared domain, there are peaks centered at around 920 nm corresponding to the intra-4f shell transition of Nd^{3+} ions from the $^4\text{F}_{3/2}$ to the $^4\text{I}_{9/2}$ level. The presence of the PL of Nd^{3+} ions after non-resonant excitation at 488 nm confirms the sensitizing effect of Si-ncs toward Nd^{3+} ions. Moreover, the most efficient emission is observed for the sample annealed at 900 °C which corresponds to the best coupling between Si-ncs and Nd^{3+} ions. It is worth to note that a notable emission from Nd^{3+} ions

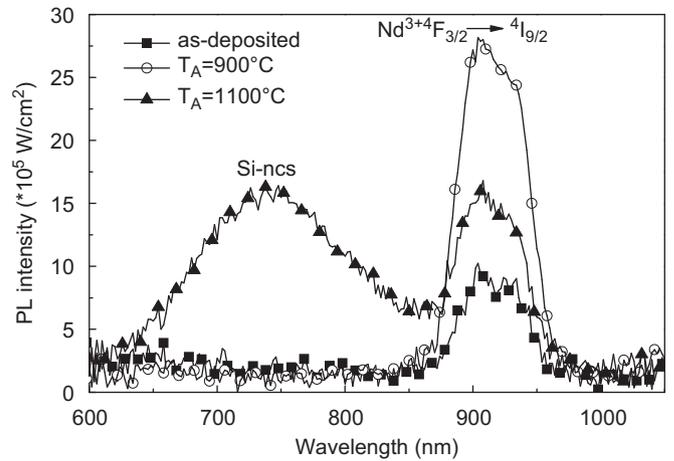


Fig. 4. Typical evolution of the PL spectra of sample with $P_{\text{Si}}=1.33 \text{ W/cm}^2$ for as-deposited and annealed films.

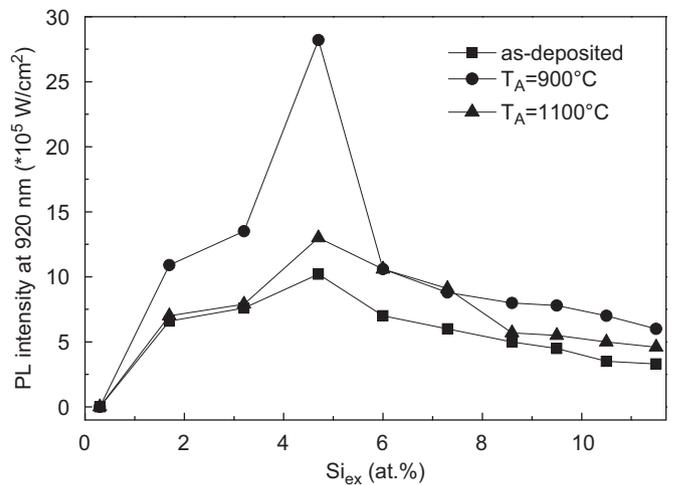


Fig. 5. Evolution of the Nd^{3+} PL intensity at 920 nm as a function of the P_{Si} for as-deposited and annealed films.

was obtained for the as-deposited sample and this fact can be explained by either formation of Si-ncs during fabrication process or by energy transfer from host defects towards RE ions [19].

In the following part, the effect of Si_{ex} on Nd^{3+} PL properties will be studied as shown in Fig. 5. The Nd^{3+} PL intensity shows first an increase with Si_{ex} for all as-deposited and annealed samples, up to a maximum corresponding to sample with $\text{Si}_{\text{ex}}=4.7\%$ ($P_{\text{Si}}=1.33 \text{ W/cm}^2$), and then decreases for higher Si_{ex} . This behavior may be explained by two reasons. On one hand, the first increase of Si_{ex} is expected to enhance the density of Si-ncs for an optimized Nd^{3+} :Si-ncs interaction. Further increase of Si_{ex} up to 11.5 at% might lead to increasing the average size of the former Si-ncs at the expense of their density and then of their coupling with Nd^{3+} ions. On the other hand, the Si incorporated into the sample may result in disorder in the host, which will favor the non-radiative channels. Besides in Fig. 5, the samples annealed at 900 °C show the highest PL intensity whatever the Si_{ex} . This observation may be ascribed to the formation of Nd_2O_3 clusters [17] for samples after annealing at high temperature ($T_{\text{A}}=1100 \text{ °C}$). To note that there is no peak for sample with $\text{Si}_{\text{ex}}=0.3 \text{ at.}\%$, possibly because the emission is too weak to be detected for the low Si_{ex} , the Nd^{3+} :Si-ncs distance is too high to allow the energy transfer process.

4. Conclusion

We have investigated the influences of Si_{ex} and T_A on the structure and optical properties of Nd-doped SRSO thin films fabricated by co-sputtering technique. It has been shown that the increase in Si_{ex} improves the Si-ncs coupling to Nd^{3+} ions, and that, it may raise the disorder in layer resulting in the increase of the number of non-radiative channels. In addition, it has been evidenced that the post annealing treatment at 900 and 1100 °C enhances the layer quality favoring the Nd^{3+} PL emission. However, high temperature annealing leads to a decrease of the Nd^{3+} emission due to the coalescence of Si-ncs and/or the formation of Nd_2O_3 cluster. Therefore, both moderate T_A and Si_{ex} are very important to be found with aim to optimize the emission from Nd^{3+} ions. In this study, the sample with $Si_{ex}=4.7$ at% ($P_{Si}=1.33$ W/cm²) shows the highest Nd^{3+} peaks after annealing at 900 °C for 1 h.

Acknowledgments

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